

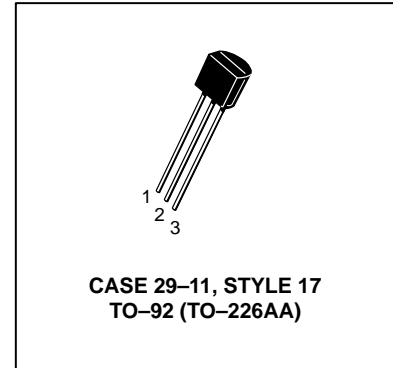
# Amplifier Transistors

## PNP Silicon

**BC327,  
BC327-16,  
BC327-25,  
BC327-40**

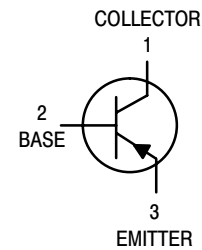
### MAXIMUM RATINGS

Rating	Symbol	BC327	Unit
Collector–Emitter Voltage	$V_{CEO}$	–45	Vdc
Collector–Base Voltage	$V_{CBO}$	–50	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–800	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$



### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ( $I_C = -10\text{ mA}, I_B = 0$ )	$V_{(BR)CEO}$	–45	–	–	Vdc
Collector–Emitter Breakdown Voltage ( $I_C = -100\ \mu\text{A}, I_E = 0$ )	$V_{(BR)CES}$	–50	–	–	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -10\ \mu\text{A}, I_C = 0$ )	$V_{(BR)EBO}$	–5.0	–	–	Vdc
Collector Cutoff Current ( $V_{CB} = -30\text{ V}, I_E = 0$ )	$I_{CBO}$	–	–	–100	nAdc
Collector Cutoff Current ( $V_{CE} = -45\text{ V}, V_{BE} = 0$ )	$I_{CES}$	–	–	–100	nAdc
Emitter Cutoff Current ( $V_{EB} = -4.0\text{ V}, I_C = 0$ )	$I_{EBO}$	–	–	–100	nAdc

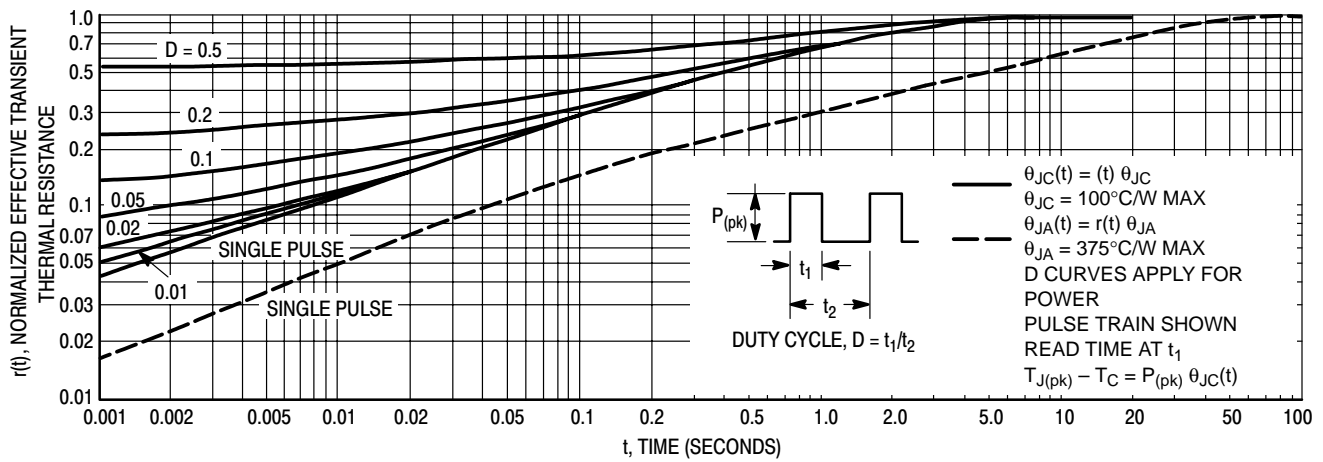
# BC327, BC327-16, BC327-25, BC327-40

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = -100\text{ mA}$ , $V_{CE} = -1.0\text{ V}$ )	BC327	100	—	630	—
	BC327-16	100	—	250	—
	BC327-25	160	—	400	—
	BC327-40	250	—	630	—
( $I_C = -300\text{ mA}$ , $V_{CE} = -1.0\text{ V}$ )		40	—	—	—
Base-Emitter On Voltage ( $I_C = -300\text{ mA}$ , $V_{CE} = -1.0\text{ V}$ )	$V_{BE(on)}$	—	—	-1.2	Vdc
Collector-Emitter Saturation Voltage ( $I_C = -500\text{ mA}$ , $I_B = -50\text{ mA}$ )	$V_{CE(sat)}$	—	—	-0.7	Vdc

## SMALL-SIGNAL CHARACTERISTICS

Output Capacitance ( $V_{CB} = -10\text{ V}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ob}$	—	11	—	pF
Current-Gain – Bandwidth Product ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ , $f = 100\text{ MHz}$ )	$f_T$	—	260	—	MHz



**Figure 1. Thermal Response**

BC327, BC327-16, BC327-25, BC327-40

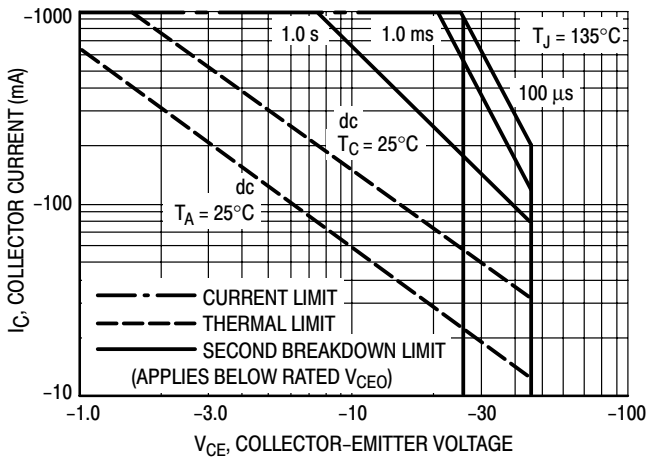


Figure 2. Active Region – Safe Operating Area

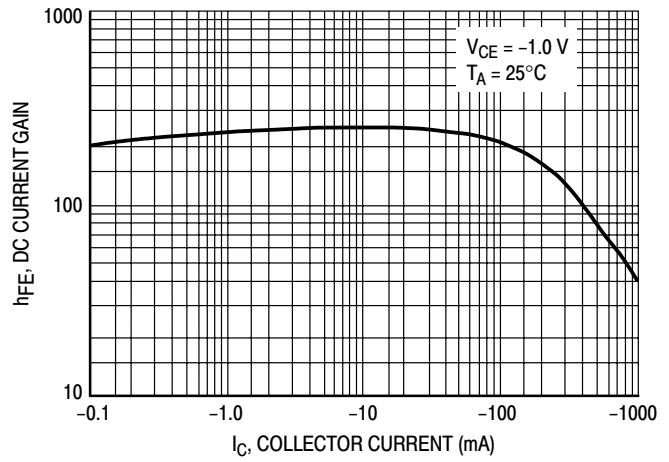


Figure 3. DC Current Gain

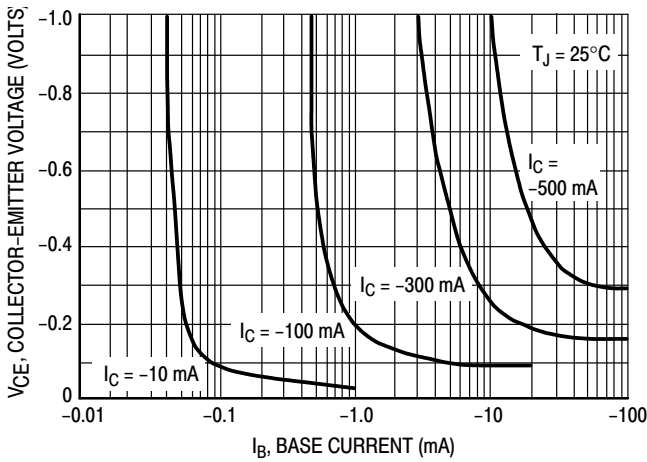


Figure 4. Saturation Region

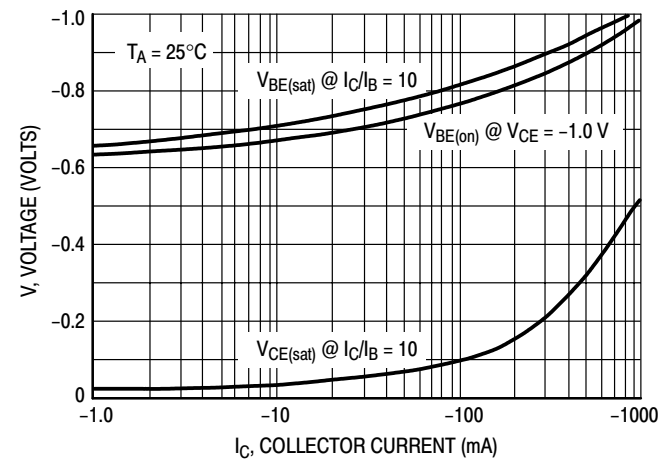


Figure 5. "On" Voltages

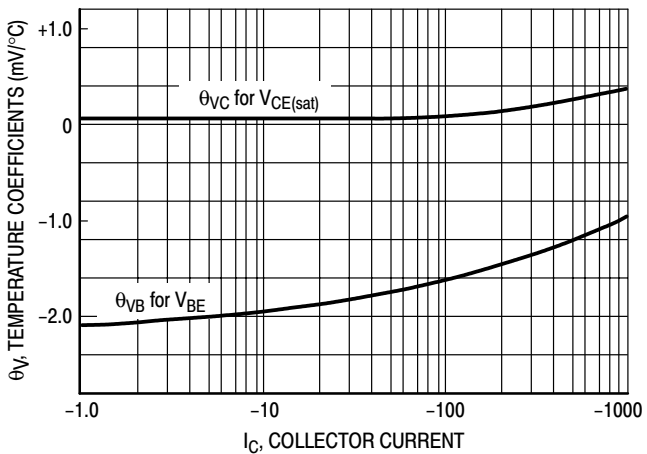


Figure 6. Temperature Coefficients

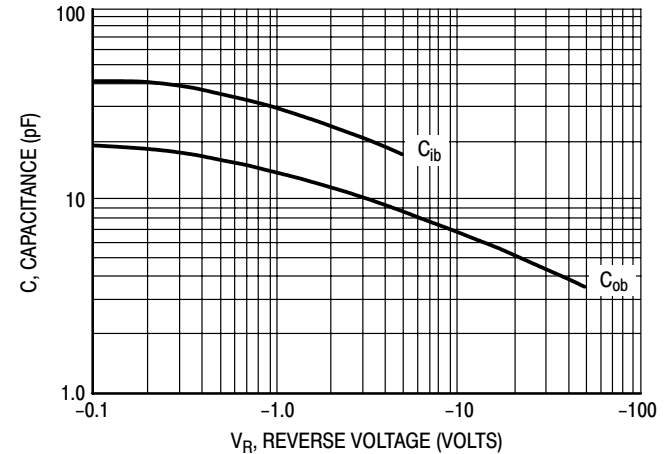


Figure 7. Capacitances